

#### 2SA1837



# Minos Silicon PNP Epitaxial Type

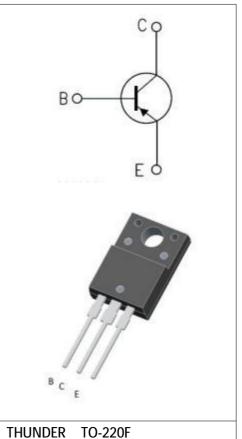
### 2SA1837

#### **Power Amplifier Applications**

- Complementary to 2SC4793
- High collector voltage:VCEO=-230V (min)

Absolute Maximum Ratings(Tc=25℃):

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Characteristics	Symbol	Rating	Unit
Collector-base voltage	<b>V</b> сво	-230	V
Collector-emitter voltage	<b>V</b> CEO	-230	V
Emitter-base voltage	<b>V</b> EBO	-5	V
Collector current	<b>l</b> c	-1	Α
Base current	I <sub>B</sub>	-0.2	Α
Collector power dissipation (Tc=25°C)	Pc	50	W
Junction temperature	Tj	150	$^{\circ}$
Storage temperature range	Тѕтс	-55~150	$^{\circ}$

#### Thermal Characteristics

Symbol	Paramter	Тур	Units
$R_{ heta$ JC	Junction-to-Case	3.0	°C/W

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## Electrical Characteristics (Tc=25℃):

Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
Collector-Base Cut-off Current	Ісво	V <sub>CB</sub> =-230V,I <sub>E</sub> =0			-1.0	uA
Emitter-Base Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V,Ic=0			-1.0	uA
Collector-Emitter Breakdown Voltage	Vceo	Ic=-1mA	-230			V
DC current gain	hfe	Ic=-0.1A; Vc==-5V	100		300	
Collector-emitter saturation voltage	Vcesat	Ic=-0.5A; IB=-0.05A			-0.5	V
Base-Emitter Saturation Voltage	<b>V</b> <sub>BEsat</sub>	Ic=-0.5A,I <sub>B</sub> =-0.05A			-1.4	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-5V;I <sub>C</sub> =-0.5A			-1.5	V
Transition frequency	f⊤	V <sub>CE</sub> =-10V;I <sub>C</sub> =-100mA		40		WHz

## Package Information

#### TO-220F PACKAGE

Symbol	Dimensions(millimeters)		
Syllibor	Min.	Max.	
Α	4.35	4.75	
A1	2.30	2.70	
A2	0.40	0.80	
A3	2.10	2.50	
b	0.60	1.00	
<b>b</b> 1	1.00	1.40	
С	0.30	0.70	
•	2.30	2.70	
Ε	9.80	10.2	
E1	6.30	6.70	
Н	15.6	16.0	
H1	8.80	9.20	
H2	12.9	13.5	
H3	3.10	3.50	
G	3.10	3.50	
ΦР	3.10	3.50	

#### **Notice**

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